

Проф. Кришна Шенаи, истакнути амерички професор и IEEE предавач, IEEE Fellow и едитор IEEE J. Electron Devices и гост Лабораторије за дигитално управљање ЕПП (ddc@etf.rs) одржаће предавање на Електротехничком факултету у Београду

у понедељак, 21. октобра у сали 61 са почетком у 12:00.

High-Density Power Conversion: Fundamentals and Challenges

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Abstract

Miniaturization of power electronics systems is one of the greatest opportunities of the 21st century global economy for a wide range of terrestrial and space applications including smart grids, motor drives, power supplies, and electric vehicles. This one-hour talk will discuss the fundamentals of and challenges in high-density power conversion using advanced silicon and wide bandgap (WBG) power semiconductor switching devices.

Speaker Biography



Krishna Shenai earned his B. Tech. (electronics) degree from IIT-Madras in 1979, MS (EE) degree from the University of Maryland – College Park, Maryland (USA) in 1981, and PhD (EE) degree from Stanford University, Stanford, California (USA) in 1986. For over 40 years, Dr. Shenai and his students have made seminal contributions to silicon and wide bandgap (WBG) power electronics technologies that have shaped the world-wide industry. He is a Fellow of IEEE, a Fellow of American Association for the Advancement of Science (AAAS), a Fellow of the American Physical Society (APS), and a member of the Academy of Engineers of Serbia (AES). Dr. Shenai currently serves as a Distinguished Lecturer of IEEE Power Electronics Society (PELS) and as an Editor of IEEE J. Electron Devices Society (EDS). He has authored over 450 peer-reviewed archived papers in top international conference digests and journals, 10 books, 9 book chapters, and holds 12 issued US patents.